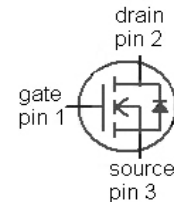


**OptiMOS<sup>®</sup> 2 Power-Transistor**
**Features**

- N-channel, logic level
- Excellent gate charge  $\times R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target application
- Ideal for high-frequency switching and synchronous rectification

**Product Summary**

|                  |      |            |
|------------------|------|------------|
| $V_{DS}$         | 100  | V          |
| $R_{DS(on),max}$ | 15.7 | m $\Omega$ |
| $I_D$            | 54   | A          |



|                |              |
|----------------|--------------|
| <b>Type</b>    | IPP16CN10L G |
|                |              |
| <b>Package</b> | PG-TO220-3   |
| <b>Marking</b> | 16CN10L      |

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

| Parameter                           | Symbol            | Conditions  | Value       | Unit              |
|-------------------------------------|-------------------|---|-------------|-------------------|
| Continuous drain current            | $I_D$             | $T_C=25\text{ °C}$  | 54          | A                 |
|                                     |                   | $T_C=100\text{ °C}$   | 38          |                   |
| Pulsed drain current <sup>2)</sup>  | $I_{D,pulse}$     | $T_C=25\text{ °C}$  | 216         |                   |
| Avalanche energy, single pulse      | $E_{AS}$          | $I_D=54\text{ A}$ , $R_{GS}=25\ \Omega$   | 105         | mJ                |
| Reverse diode $dv/dt$               | $dv/dt$           | $I_D=53\text{ A}$ , $V_{DS}=80\text{ V}$ ,<br>$di/dt=100\text{ A}/\mu\text{s}$ ,<br>$T_{j,max}=175\text{ °C}$ | 6           | kV/ $\mu\text{s}$ |
| Gate source voltage <sup>3)</sup>   | $V_{GS}$          |   | $\pm 20$    | V                 |
| Power dissipation                   | $P_{tot}$         | $T_C=25\text{ °C}$  | 100         | W                 |
| Operating and storage temperature   | $T_j$ , $T_{stg}$ |   | -55 ... 175 | °C                |
| IEC climatic category; DIN IEC 68-1 |                   |   | 55/175/56   |                   |

<sup>1)</sup>J-STD20 and JESD22

<sup>2)</sup> see figure 3

<sup>3)</sup>  $T_{j,max}=150\text{ °C}$  and duty cycle  $D=0.01$  for  $V_{GS}<-5\text{ V}$

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|  |            |  |   |   |     |     |
|--|------------|--|---|---|-----|-----|
| Thermal resistance, junction - case    | $R_{thJC}$ |  | - | - | 1.5 | K/W |
| Thermal resistance, junction - ambient | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|  |            | 6 cm <sup>2</sup> cooling area <sup>4)</sup> | - | - | 40  |     |

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

**Static characteristics**

|                                  |               |  |     |      |      |               |
|----------------------------------|---------------|--|-----|------|------|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                       | 100 | -    | -    | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=61\text{ }\mu\text{A}$                 | 1.2 | 1.84 | 2.4  |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$  | -   | 0.1  | 1    | $\mu\text{A}$ |
|                                  |               | $V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$ | -   | 10   | 100  |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                    | -   | 1    | 100  | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=4.5\text{ V}, I_D=27\text{ A}$                     | -   | 15.3 | 20.8 | m $\Omega$    |
|                                  |               | $V_{GS}=10\text{ V}, I_D=54\text{ A}$                      | -   | 12.9 | 15.7 |               |
| Gate resistance                  | $R_G$         |  | -   | 1.1  | -    | $\Omega$      |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=54\text{ A}$            | 45  | 89   | -    | S             |

<sup>4)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |   |   |      |      |    |
|------------------------------|--------------|---|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=50\text{ V},$<br>$f=1\text{ MHz}$                    | - | 3150 | 4190 | pF |
| Output capacitance           | $C_{oss}$    |   | - | 393  | 523  |    |
| Reverse transfer capacitance | $C_{rss}$    |   | - | 23   | -    |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=53\text{ A}, R_G=1.6\ \Omega$ | - | 11   | -    | ns |
| Rise time                    | $t_r$        |   | - | 8    | -    |    |
| Turn-off delay time          | $t_{d(off)}$ |   | - | 30   | -    |    |
| Fall time                    | $t_f$        |   | - | 4    | -    |    |

**Gate Charge Characteristics<sup>5)</sup>**

|                       |               |  |   |     |   |    |
|-----------------------|---------------|--|---|-----|---|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=50\text{ V}, I_D=53\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 12  | - | nC |
| Gate to drain charge  | $Q_{gd}$      |  | - | 7   | - |    |
| Switching charge      | $Q_{sw}$      |  | - | 10  | - |    |
| Gate charge total     | $Q_g$         |  | - | 44  | - |    |
| Gate plateau voltage  | $V_{plateau}$ |  | - | 3.7 | - | V  |
| Output charge         | $Q_{oss}$     | $V_{DD}=50\text{ V}, V_{GS}=0\text{ V}$                                    | - | 40  | - | nC |

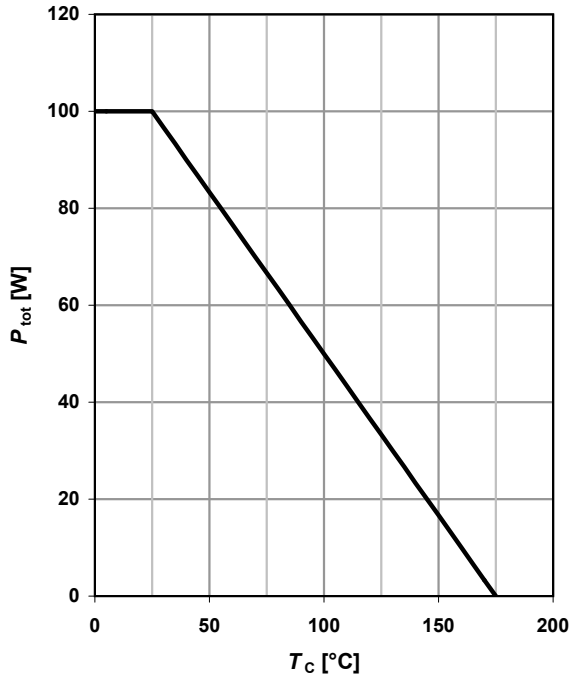
**Reverse Diode**

|                                  |               |   |   |     |     |    |
|----------------------------------|---------------|---|---|-----|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ }^\circ\text{C}$  | - | -   | 54  | A  |
| Diode pulse current              | $I_{S,pulse}$ |   | - | -   | 216 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=54\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$ | - | 1   | 1.2 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=50\text{ V}, I_F=I_S,$<br>$di_F/dt=100\text{ A}/\mu\text{s}$       | - | 103 | -   | ns |
| Reverse recovery charge          | $Q_{rr}$      |   | - | 215 | -   | nC |

<sup>5)</sup> See figure 16 for gate charge parameter definition

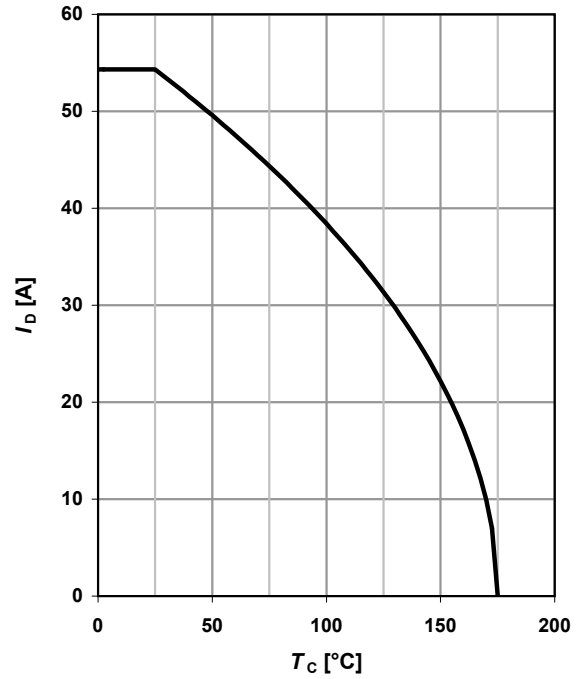
**1 Power dissipation**

$$P_{tot}=f(T_C)$$



**2 Drain current**

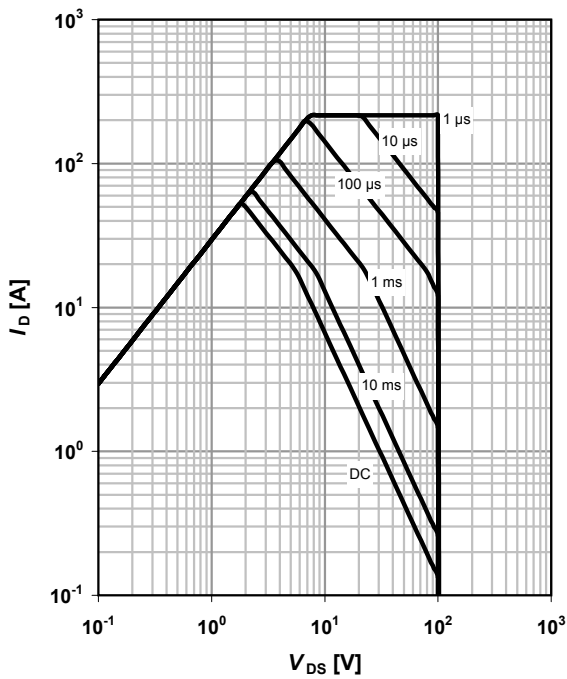
$$I_D=f(T_C); V_{GS}\geq 10\text{ V}$$



**3 Safe operating area**

$$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$$

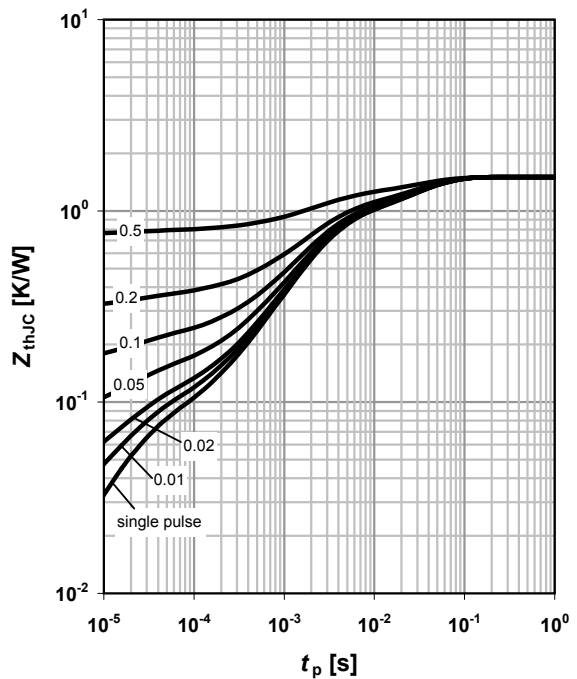
parameter:  $t_p$



**4 Max. transient thermal impedance**

$$Z_{thJC}=f(t_p)$$

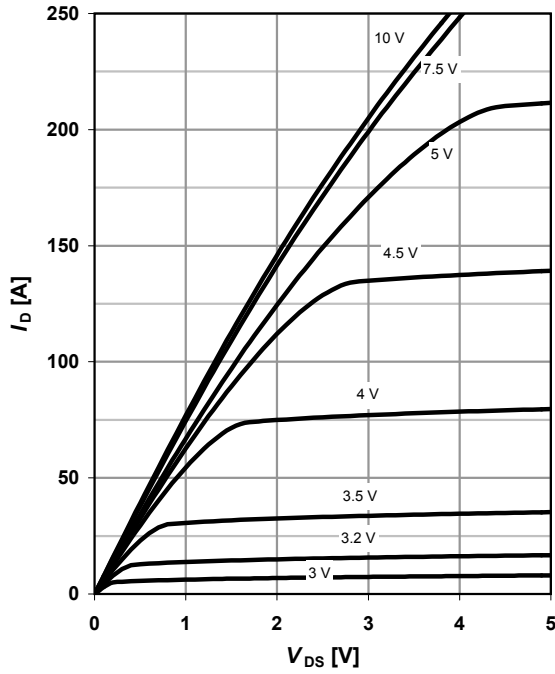
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$$

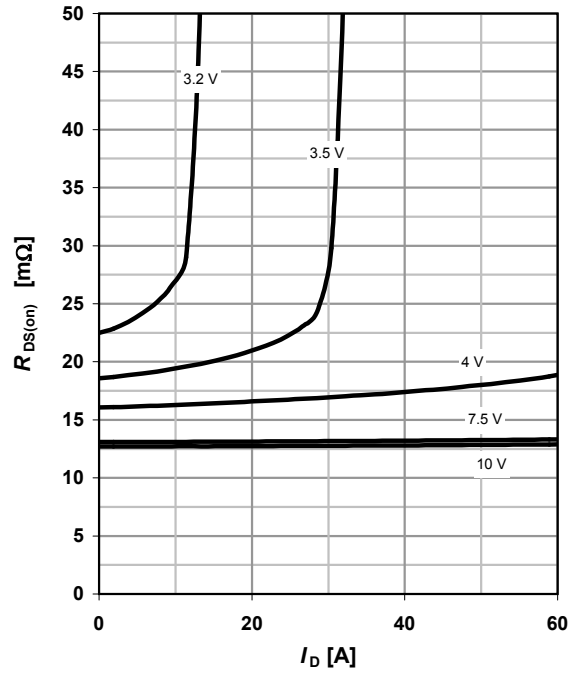
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$$

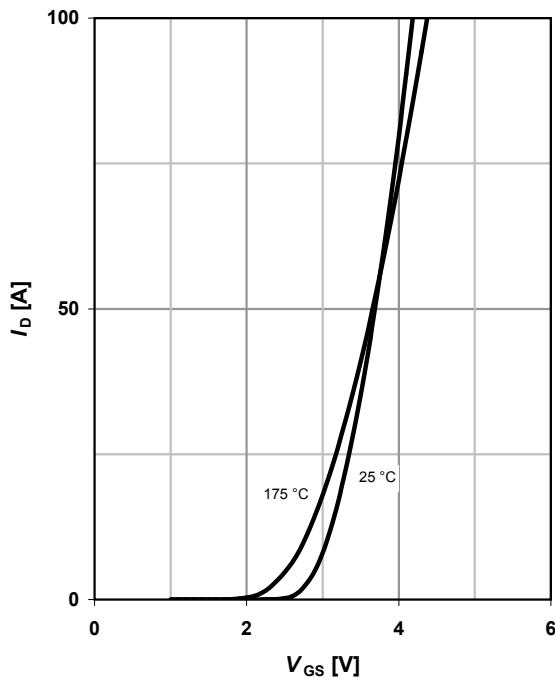
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

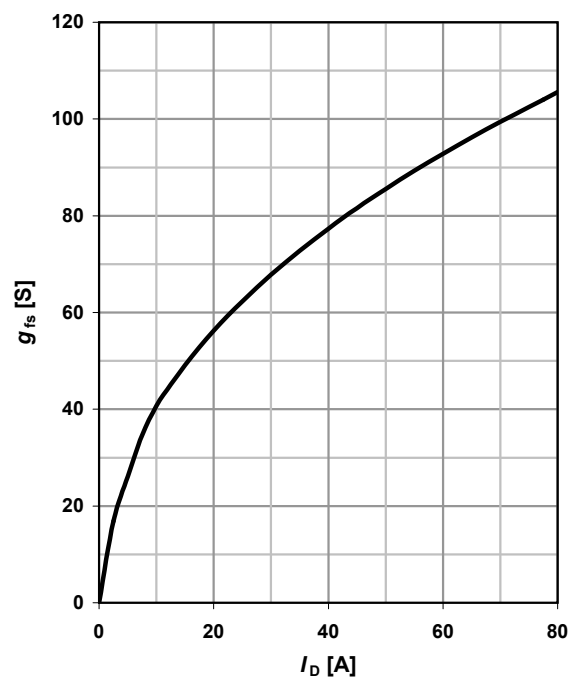
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

parameter:  $T_j$



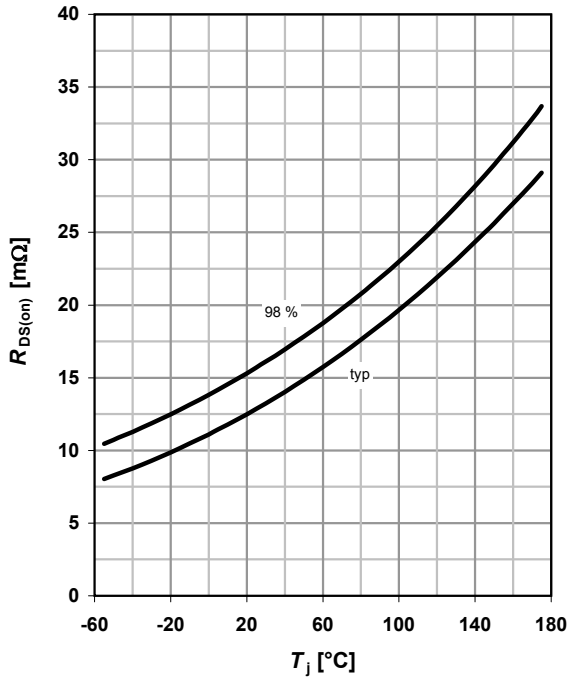
**8 Typ. forward transconductance**

$$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$$



**9 Drain-source on-state resistance**

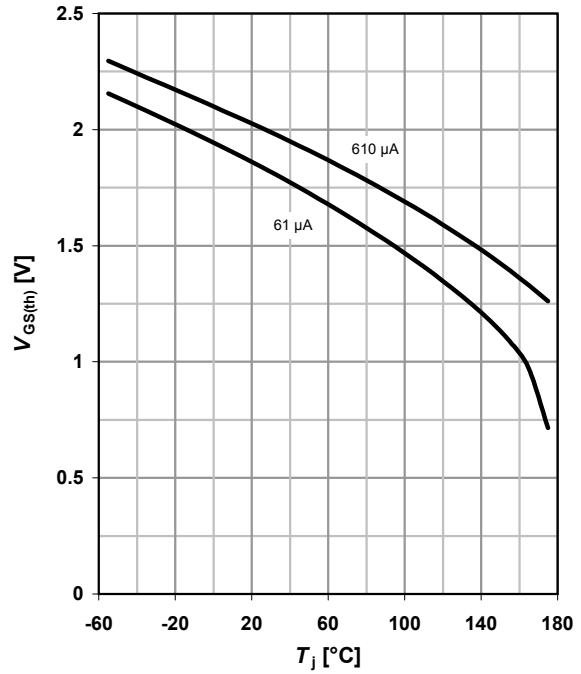
$R_{DS(on)} = f(T_j); I_D = 54 \text{ A}; V_{GS} = 10 \text{ V}$



**10 Typ. gate threshold voltage**

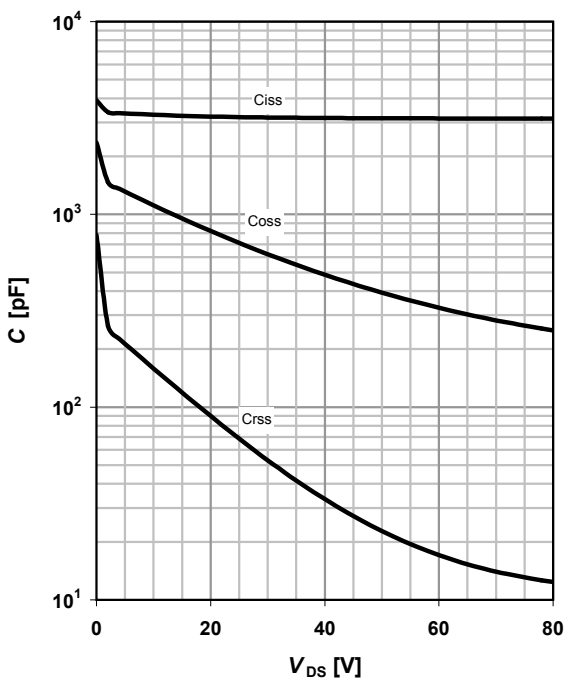
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

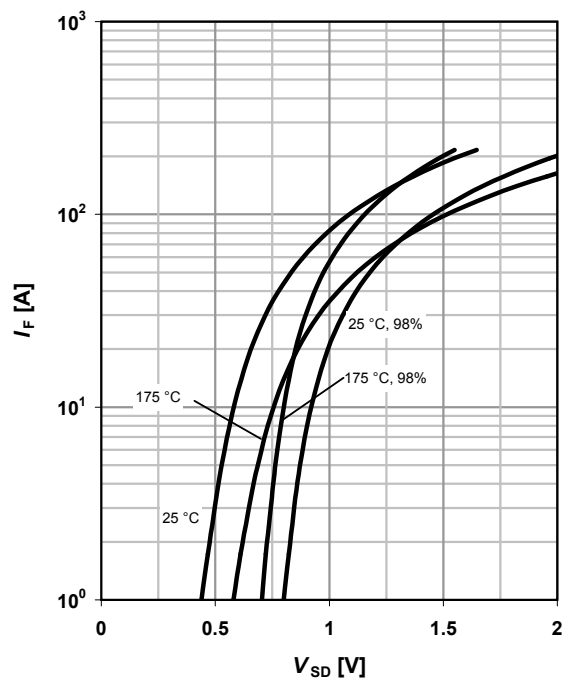
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

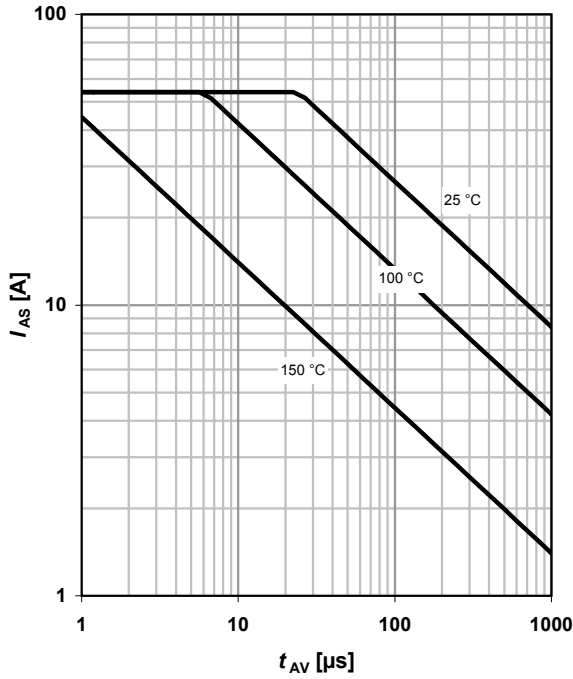
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

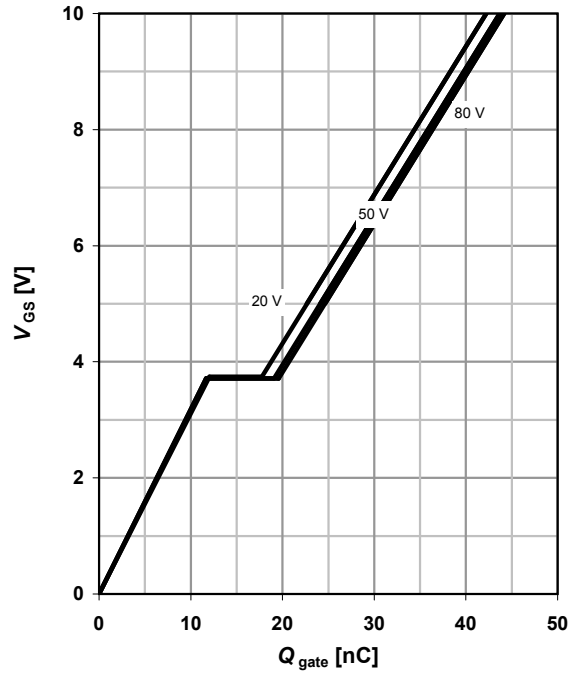
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

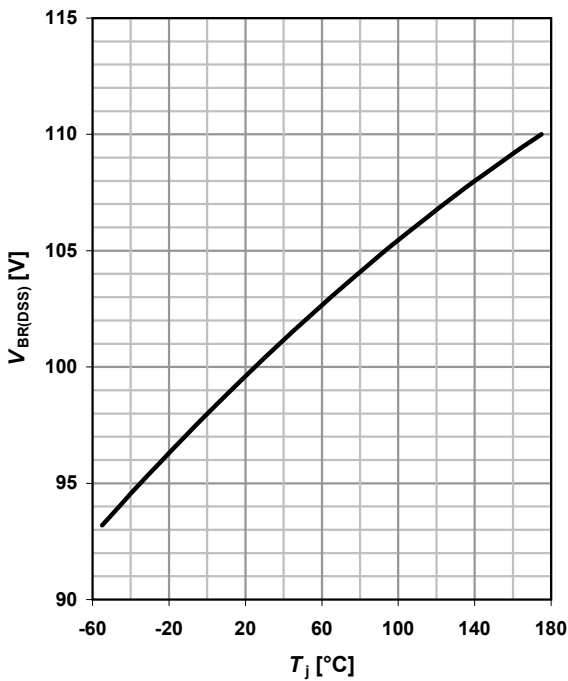
$V_{GS}=f(Q_{gate}); I_D=54 \text{ A pulsed}$

parameter:  $V_{DD}$



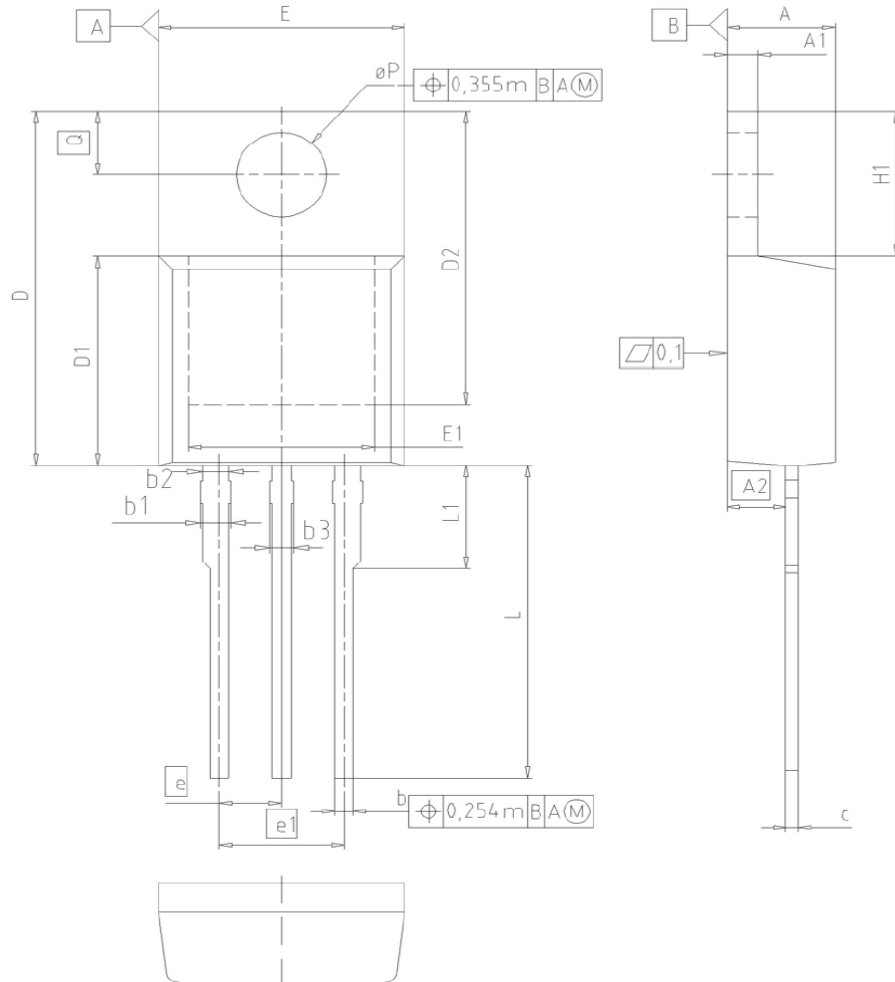
**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



**16 Gate charge waveforms**



**PG-TO220-3: Outline**


| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.30        | 4.57  | 0.169  | 0.180 |
| A1  | 1.17        | 1.40  | 0.046  | 0.055 |
| A2  | 2.15        | 2.72  | 0.085  | 0.107 |
| b   | 0.65        | 0.86  | 0.026  | 0.034 |
| b1  | 0.95        | 1.40  | 0.037  | 0.055 |
| b2  | 0.95        | 1.15  | 0.037  | 0.045 |
| b3  | 0.65        | 1.15  | 0.026  | 0.045 |
| c   | 0.33        | 0.60  | 0.013  | 0.024 |
| D   | 14.81       | 15.95 | 0.583  | 0.628 |
| D1  | 8.51        | 9.45  | 0.335  | 0.372 |
| D2  | 12.19       | 13.10 | 0.480  | 0.516 |
| E   | 9.70        | 10.36 | 0.382  | 0.408 |
| E1  | 6.50        | 8.60  | 0.256  | 0.339 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 3           |       | 3      |       |
| H1  | 5.90        | 6.90  | 0.232  | 0.272 |
| L   | 13.00       | 14.00 | 0.512  | 0.551 |
| L1  | -           | 4.80  | -      | 0.189 |
| øP  | 3.60        | 3.89  | 0.142  | 0.153 |
| Q   | 2.60        | 3.00  | 0.102  | 0.118 |

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